



PMGD175XNE

30 V, Dual N-channel Trench MOSFET

15 April 2016

Product data sheet

1. General description

Dual N-channel enhancement mode Field-Effect Transistor (FET) in a very small SOT363 (TSSOP6) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Low threshold voltage
- Very fast switching
- Trench MOSFET technology
- ElectroStatic Discharge (ESD) protection > 2 kV HBM

3. Applications

- Relay driver
- High-speed line driver
- Low-side loadswitch
- Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Per transistor						
V_{DS}	drain-source voltage	$T_J = 25\text{ °C}$	-	-	30	V
V_{GS}	gate-source voltage		-12	-	12	V
I_D	drain current	$V_{GS} = 4.5\text{ V}; T_{amb} = 25\text{ °C}; t \leq 5\text{ s}$	[1]	-	0.95	A
Static characteristics (per transistor)						
R_{DSon}	drain-source on-state resistance	$V_{GS} = 4.5\text{ V}; I_D = 0.9\text{ A}; T_J = 25\text{ °C}$	-	211	252	m Ω

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².

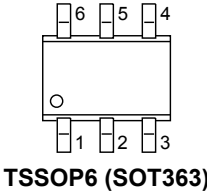
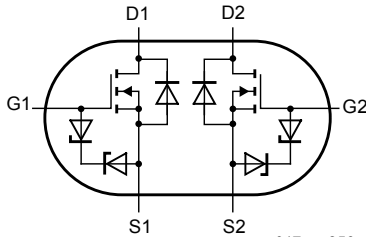


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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source TR1	 <p>TSSOP6 (SOT363)</p>	 <p>017aaa256</p>
2	G1	gate TR1		
3	D2	drain TR2		
4	S2	source TR2		
5	G2	gate TR2		
6	D1	drain TR1		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PMGD175XNE	TSSOP6	plastic surface-mounted package; 6 leads	SOT363

7. Marking

Table 4. Marking codes

Type number	Marking code
PMGD175XNE	LU%

[1] % = placeholder for manufacturing site code

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transistor						
V _{DS}	drain-source voltage	T _j = 25 °C		-	30	V
V _{GS}	gate-source voltage			-12	12	V
I _D	drain current	V _{GS} = 4.5 V; T _{amb} = 25 °C; t ≤ 5 s	[1]	-	0.95	A
		V _{GS} = 4.5 V; T _{amb} = 25 °C	[1]	-	0.87	A
		V _{GS} = 4.5 V; T _{amb} = 100 °C	[1]	-	0.5	A
I _{DM}	peak drain current	T _{amb} = 25 °C; single pulse; t _p ≤ 10 μs		-	4	A
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	260	mW
			[1]	-	310	mW
		T _{sp} = 25 °C		-	905	mW
Per device						
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	390	mW
T _j	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drain diode						
I _S	source current	T _{amb} = 25 °C	[1]	-	0.31	A

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.



Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$



Fig. 2. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$

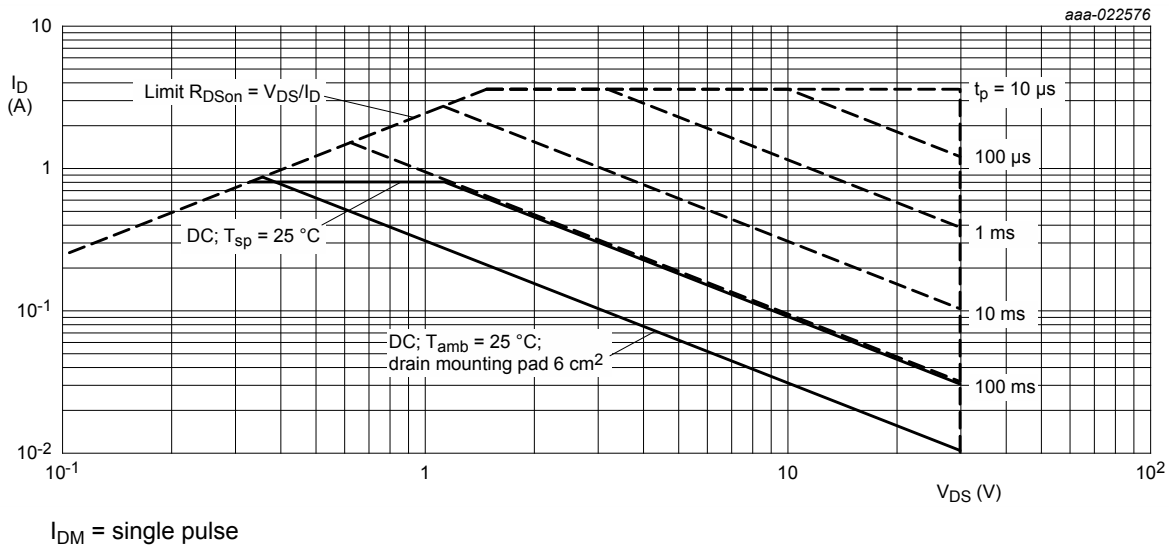


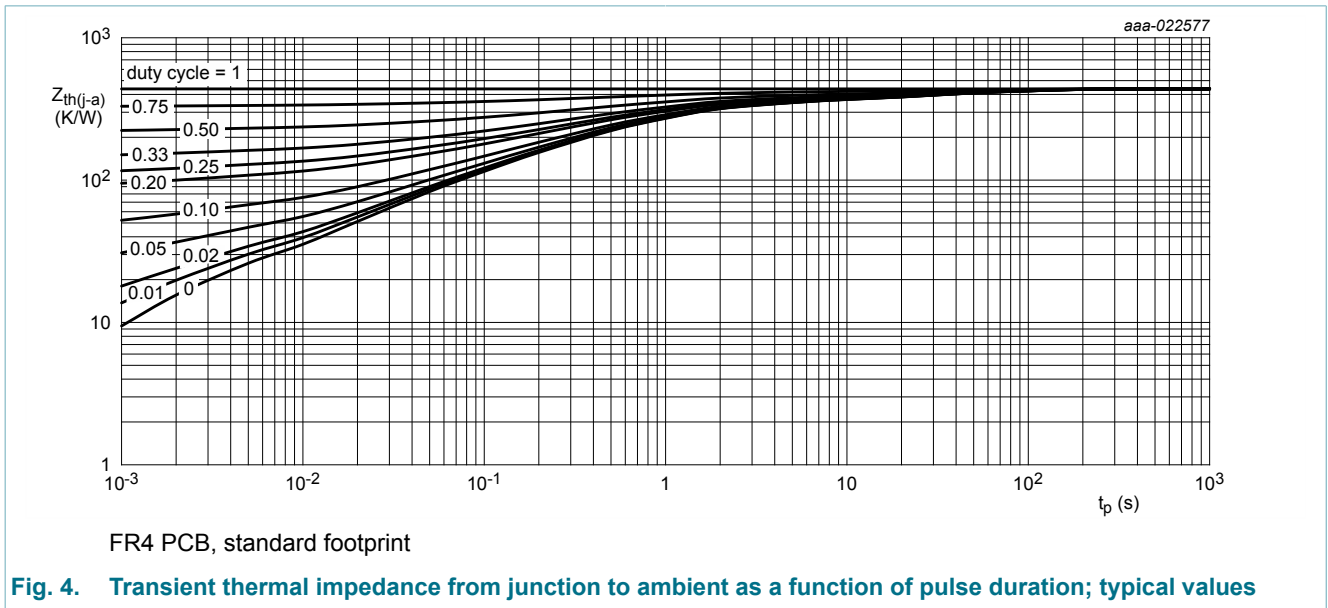
Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

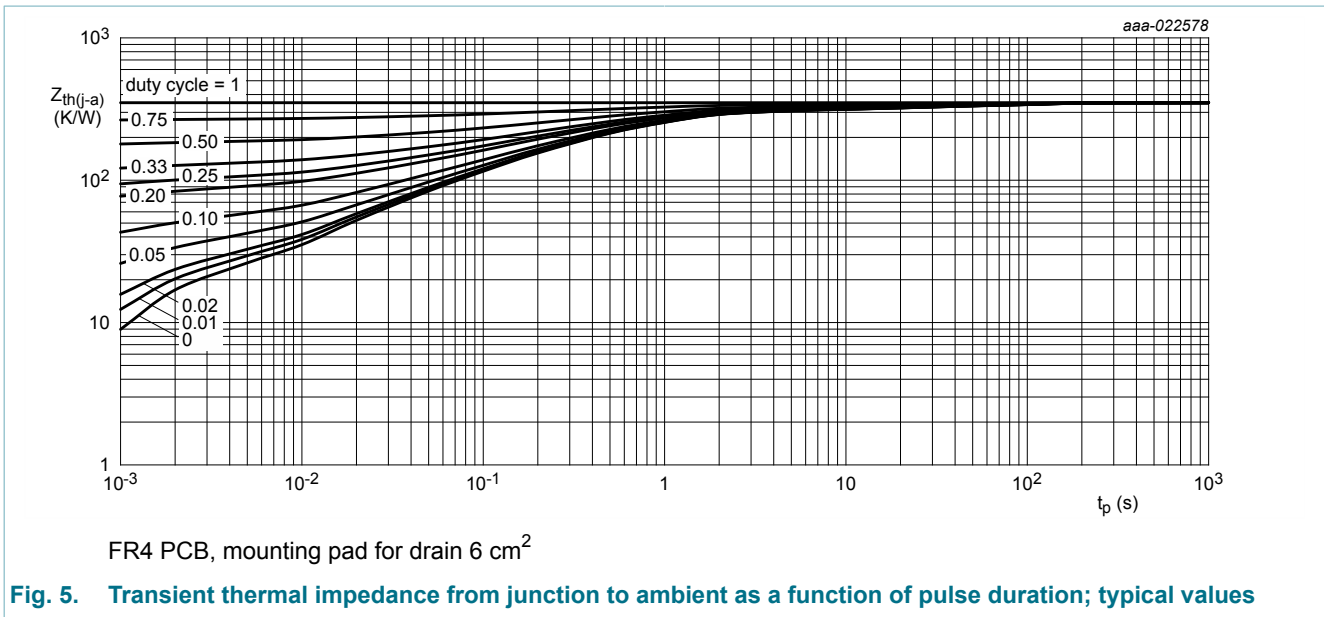
9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Per transistor							
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	[1]	-	417	480	K/W
			[2]	-	352	405	K/W
		in free air; t ≤ 5 s	[2]	-	295	340	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	120	138	K/W
Per device							
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	[1]	-	-	320	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².





10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics (per transistor)						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$	30	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ }^\circ C$	0.75	1	1.25	V
I_{DSS}	drain leakage current	$V_{DS} = 30 V; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$	-	-	1	μA
I_{GSS}	gate leakage current	$V_{GS} = 12 V; V_{DS} = 0 V; T_j = 25 \text{ }^\circ C$	-	-	10	μA
		$V_{GS} = -12 V; V_{DS} = 0 V; T_j = 25 \text{ }^\circ C$	-	-	-10	μA
		$V_{GS} = 4.5 V; V_{DS} = 0 V; T_j = 25 \text{ }^\circ C$	-	-	5	μA
		$V_{GS} = -4.5 V; V_{DS} = 0 V; T_j = 25 \text{ }^\circ C$	-	-	-5	μA
R_{DSon}	drain-source on-state resistance	$V_{GS} = 4.5 V; I_D = 0.9 A; T_j = 25 \text{ }^\circ C$	-	211	252	m Ω
		$V_{GS} = 4.5 V; I_D = 0.9 A; T_j = 150 \text{ }^\circ C$	-	344	411	m Ω
		$V_{GS} = 2.5 V; I_D = 0.8 A; T_j = 25 \text{ }^\circ C$	-	267	319	m Ω
g_{fs}	forward transconductance	$V_{DS} = 10 V; I_D = 0.9 A; T_j = 25 \text{ }^\circ C$	-	3.5	-	S
Dynamic characteristics (per transistor)						
$Q_{G(tot)}$	total gate charge	$V_{DS} = 15 V; I_D = 0.9 A; V_{GS} = 4.5 V; T_j = 25 \text{ }^\circ C$	-	1.05	1.65	nC
Q_{GS}	gate-source charge		-	0.15	-	nC
Q_{GD}	gate-drain charge		-	0.27	-	nC
C_{iss}	input capacitance	$V_{DS} = 15 V; f = 1 \text{ MHz}; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$	-	81	-	pF
C_{oss}	output capacitance		-	13	-	pF
C_{rss}	reverse transfer capacitance		-	9	-	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = 15 V; I_D = 0.9 A; V_{GS} = 4.5 V; R_{G(ext)} = 6 \Omega; T_j = 25 \text{ }^\circ C$	-	7	-	ns
t_r	rise time		-	14	-	ns
$t_{d(off)}$	turn-off delay time		-	17	-	ns
t_f	fall time		-	6	-	ns
Source-drain diode (per transistor)						
V_{SD}	source-drain voltage	$I_S = 0.3 A; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$	-	0.7	1.2	V

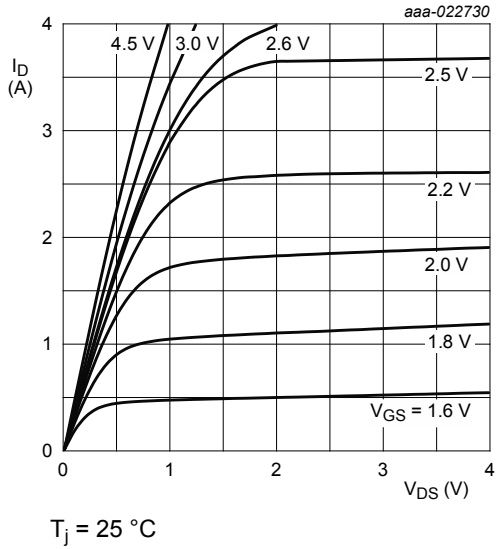


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

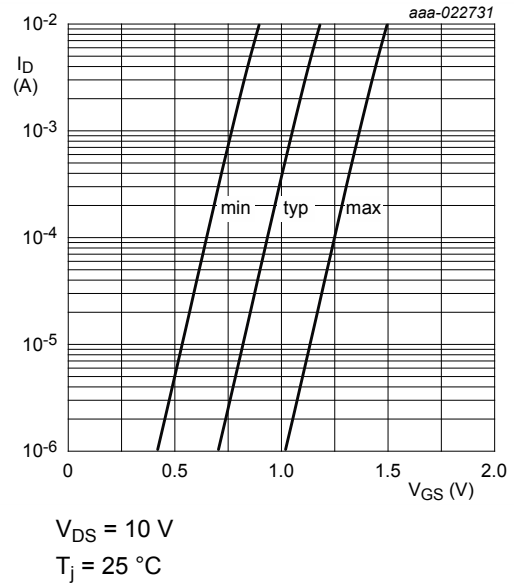


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

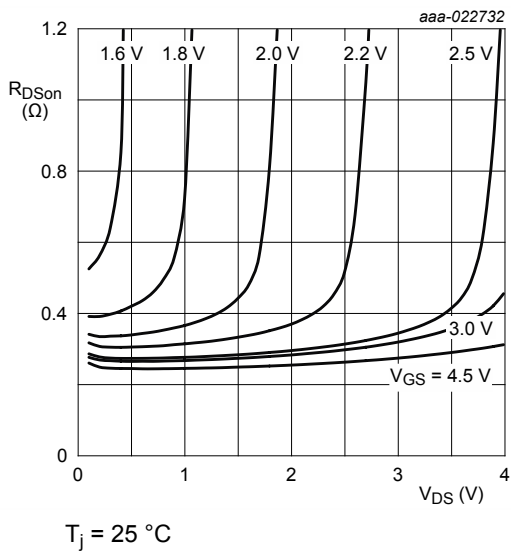


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

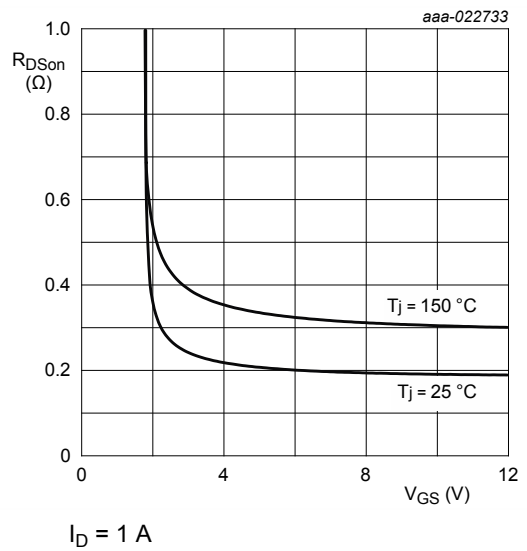


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

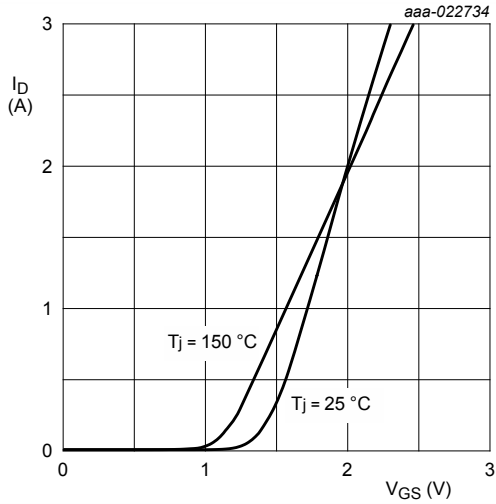


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

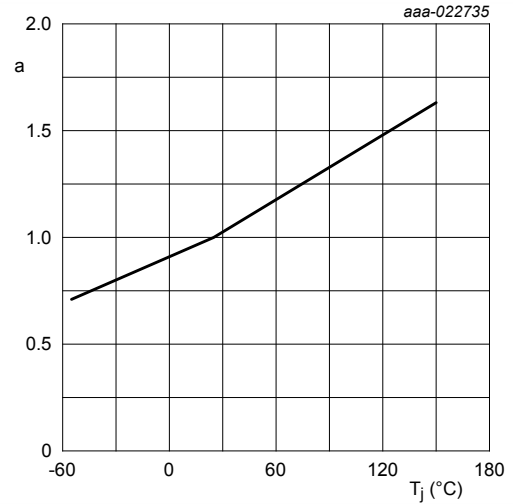


Fig. 11. Normalized drain-source on-state resistance as a function of ambient temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25\text{ }^{\circ}\text{C})}}$$

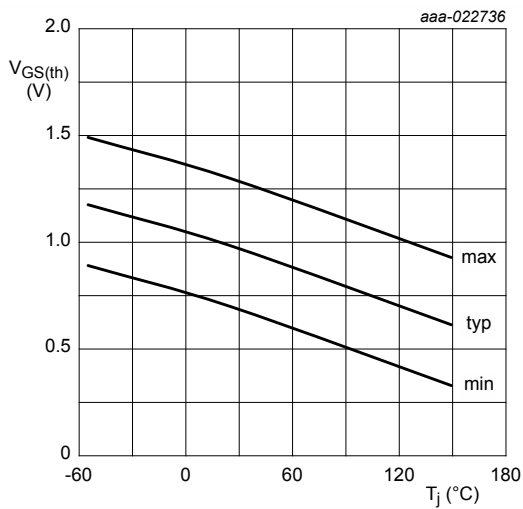


Fig. 12. Gate-source threshold voltage as a function of ambient temperature

$I_D = 250 \mu\text{A}; V_{DS} = V_{GS}$

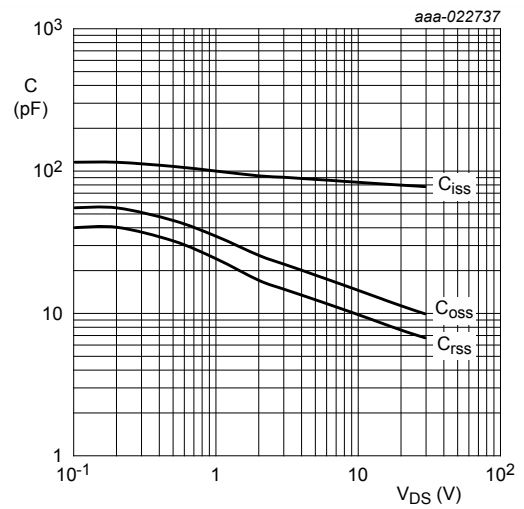
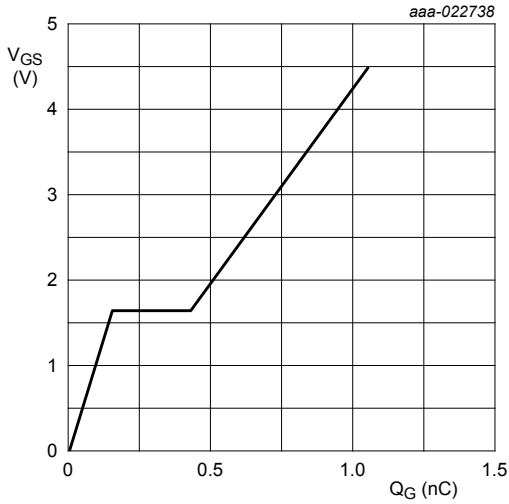


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$f = 1 \text{ MHz}; V_{GS} = 0 \text{ V}$



$V_{DS} = 15\text{ V}; I_D = 0.91\text{ A}$

Fig. 14. Gate-source voltage as a function of gate charge; typical values

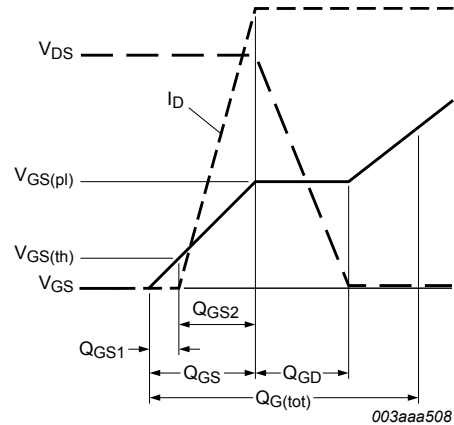
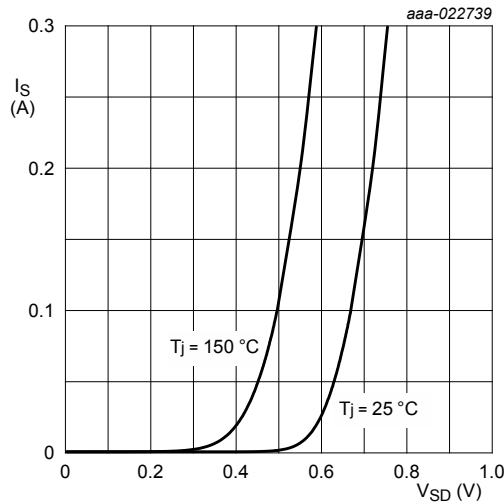


Fig. 15. Gate charge waveform definitions



$V_{GS} = 0\text{ V}$

Fig. 16. Source current as a function of source-drain voltage; typical values

11. Test information

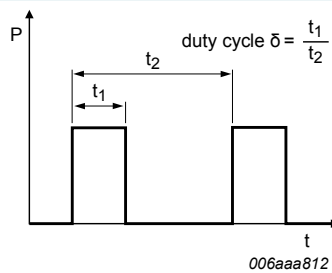


Fig. 17. Duty cycle definition

12. Package outline

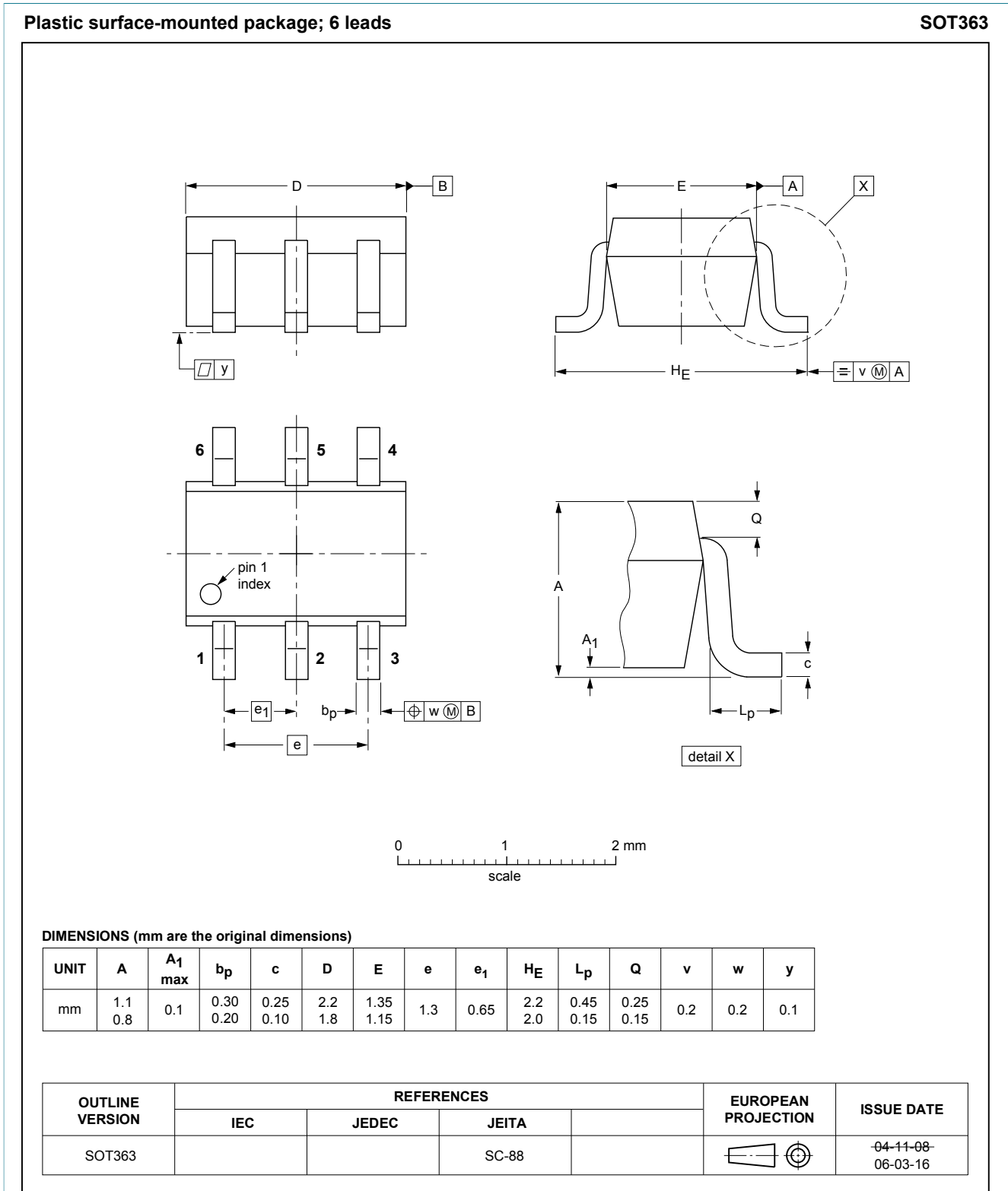


Fig. 18. Package outline TSSOP6 (SOT363)

13. Soldering

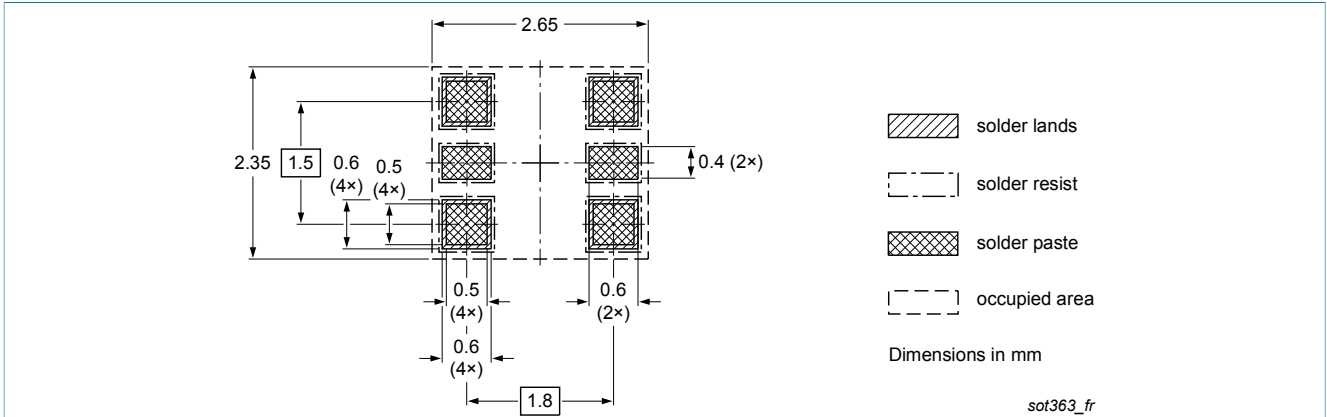


Fig. 19. Reflow soldering footprint for TSSOP6 (SOT363)

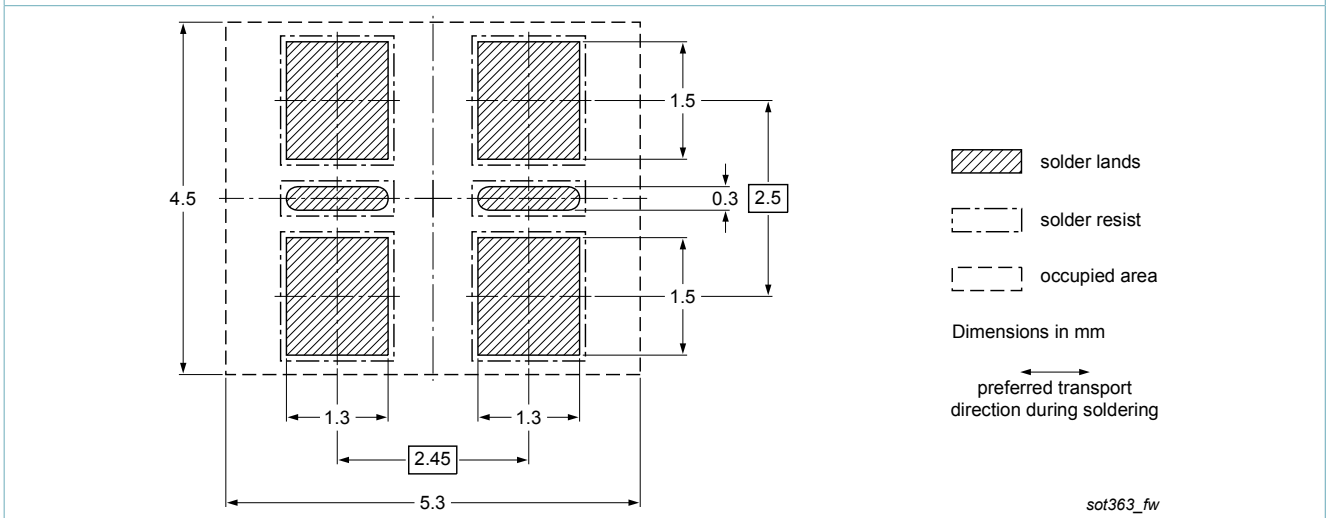


Fig. 20. Wave soldering footprint for TSSOP6 (SOT363)

14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMGD175XNE v.1	20160415	Product data sheet	-	-

15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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